



#### 60V Dual N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

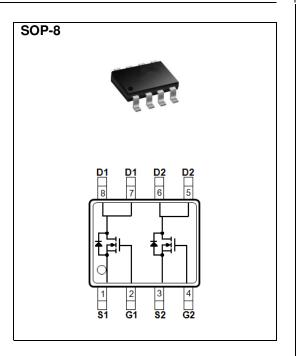
6 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@5.5A<21m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @4.5V,  $I_{D}$ @3A<24m $\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOP-8 package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams



# $\textbf{Maximum Ratings and Thermal Characteristics} \; (T_{A} = 25 ^{\circ} \text{C unless otherwise noted})$

PARAMET	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		$V_{DS}$	60	.,	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>A</sub> =25°C		6		
	T <sub>A</sub> =70°C	I <sub>D</sub>	5	Α	
Pulsed Drain Current (Note 1,3)		I <sub>DM</sub>	22	]	
Power Dissipation	T <sub>A</sub> =25°C	1	1.7	W	
	T <sub>A</sub> =70°C	P <sub>D</sub>	1.1		
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 5)		$R_{\theta JA}$	73.5	°C/W	





## Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			_			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.73	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 5.5A$	-	18	21	0
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =4.5V, $I_{D}$ =3.0A	-	- 21 24 mΩ	11177	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =60V, $V_{GS}$ =0V	-	-	1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =30V, I <sub>D</sub> =5.5A, V <sub>GS</sub> =10V (Note 1,2)	-	28	-	nC
Gate-Source Charge	$Q_gs$		-	3.5	-	
Gate-Drain Charge	$Q_gd$		-	6.5	-	
Input Capacitance	Ciss	V 20V V 0V	-	1680	-	pF
Output Capacitance	Coss	$V_{DS}$ =20V, $V_{GS}$ =0V, $f$ =1.0MHZ	-	115	-	
Reverse Transfer Capacitance	Crss		-	85	-	
Turn-On Delay Time	td <sub>(on)</sub>	V 20V I 1A	-	7.2	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =30V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	38	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	34	-	
Turn-Off Fall Time	tf		-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,		-	-	6	Α
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

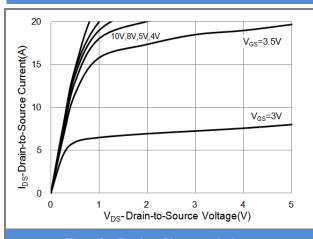
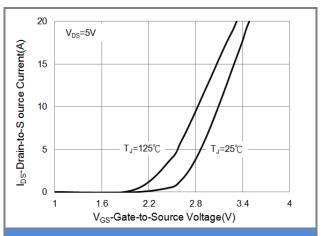


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

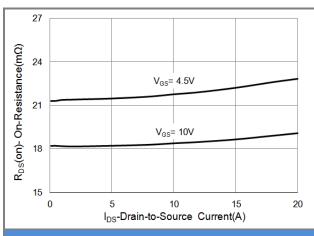


Fig.3 On-Resistance vs. Drain Current

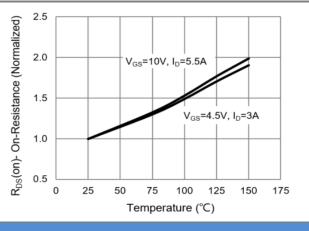


Fig.4 On-Resistance vs. Junction temperature

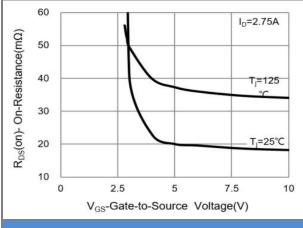
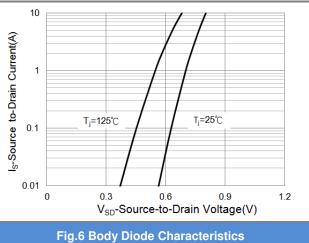


Fig.5 On-Resistance Variation with V<sub>GS</sub>







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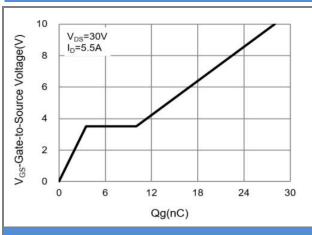


Fig.7 Gate-Charge Characteristics

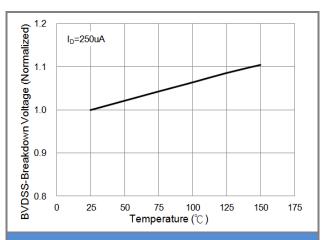


Fig.8 Breakdown Voltage Variation vs. Temperature

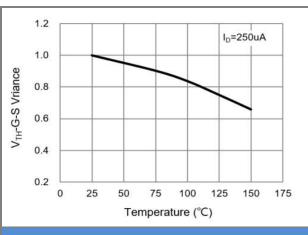


Fig.9 Threshold Voltage Variation with Temperature

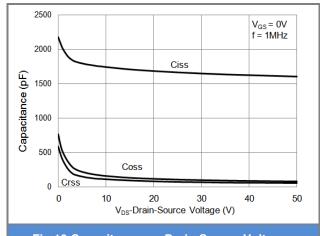
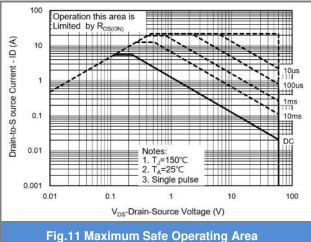


Fig.10 Capacitance vs. Drain-Source Voltage







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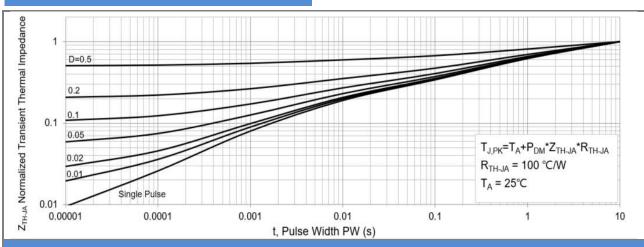


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

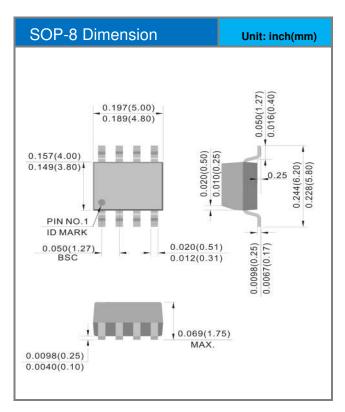


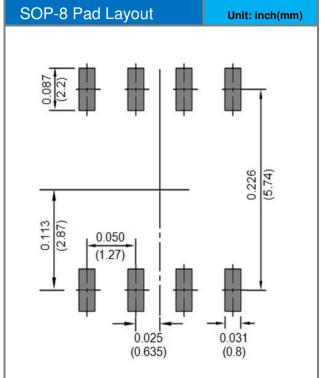


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJL9836A_R2_00001	SOP-8	2.5K pcs / 13" reel	L9836A	Halogen free

### **Packaging Information & Mounting Pad Layout**









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